

» Patents Index (CTPI) in English  
Boolean Search | Patent Number Search | Field search

540171 -- Patent Information

Published Serial No.	540171								
Title	Manufacturing method of high-power light emitting diode								
Patent type	B								
Date of Grant	2003/7/1								
Application Number	091116005								
Filing Date	2002/7/18								
IPC	H01L33/00								
Inventor	CHEN, TZER-PERNG(TW) CHANG, CHIH-SUNG(TW) YANG, KUANG-NENG(TW)								
Applicant	<table border="1"><tr><td>Name</td><td>Country</td><td>Individual/Company</td></tr><tr><td>UNITED EPITAXY CO., LTD.</td><td>TW</td><td>Company</td></tr></table>			Name	Country	Individual/Company	UNITED EPITAXY CO., LTD.	TW	Company
Name	Country	Individual/Company							
UNITED EPITAXY CO., LTD.	TW	Company							
Abstract	A method for manufacturing high-power light emitting diode that has a metal reflection layer and uses an electroplating method to form a metal substrate is disclosed in the present invention. In the invention, since a metal reflection layer is used such that light absorption problem of substrate can be avoided and the light emitting brightness also can be raised apparently. In addition, P and N electrodes can be formed respectively on a vertical structure of both upper and lower sides of the light emitting diode. Furthermore, a semiconductor substrate is changed into a metal substrate so as to greatly improve the heat dissipation characteristic of the light emitting diode and make the light emitting diode capable of being operated at a higher current.								